Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

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We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

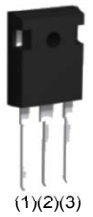
RGTVX6TS65

650V 80A Field Stop Trench IGBT Datasheet

V_{CES}	650V
$I_{C(100°C)}$	80A
$V_{CE(sat)}$ (Typ.)	1.5V
P_D	404W

●Outline

TO-247N



●Features

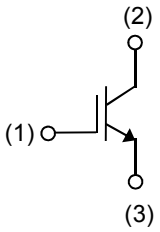
1) Low Collector - Emitter Saturation Voltage

2) High Speed Switching & Low Switching Loss

3) Short Circuit Withstand Time 2μs

4) Pb - free Lead Plating ; RoHS Compliant

●Inner Circuit



(1) Gate
(2) Collector
(3) Emitter

●Applications

Solar Inverter

UPS

Welding

IH

PFC

●Packaging Specifications

Type	Packaging	Tube
	Reel Size (mm)	-
	Tape Width (mm)	-
	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGTVX6TS65

●Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V_{CES}	650	V
Gate - Emitter Voltage		V_{GES}	±30	V
Collector Current	T_C = 25°C	I_C	144	A
	T_C = 100°C	I_C	80	A
Pulsed Collector Current		I_{CP} *1	320	A
Power Dissipation	T_C = 25°C	P_D	404	W
	T_C = 100°C	P_D	202	W
Operating Junction Temperature		T_j	−40 to +175	°C
Storage Temperature		T_{stg}	−55 to +175	°C

*1 Pulse width limited by $T_{jmax.}$

●Thermal Resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.37	°C/W

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Collector - Emitter Breakdown Voltage	BV_{CES}	I_C = 10μA, V_{GE} = 0V	650	-	-	V
Collector Cut - off Current	I_{CES}	V_{CE} = 650V, V_{GE} = 0V	-	-	10	μA
Gate - Emitter Leakage Current	I_{GES}	V_{GE} = ±30V, V_{CE} = 0V	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	V_{CE} = 5V, I_C = 57.1mA	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 80A, V_{GE} = 15V				V
		T_j = 25°C	-	1.5	1.9	
		T_j = 175°C	-	1.85	-	

●**IGBT Electrical Characteristics** (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input Capacitance	C_{ies}	V_{CE} = 30V	-	4810	-	pF
Output Capacitance	C_{oes}	V_{GE} = 0V	-	184	-	
Reverse Transfer Capacitance	C_{res}	f = 1MHz	-	79	-	
Total Gate Charge	Q_g	V_{CE} = 400V	-	171	-	nC
Gate - Emitter Charge	Q_{ge}	I_C = 80A	-	33	-	
Gate - Collector Charge	Q_{gc}	V_{GE} = 15V	-	59	-	
Turn - on Delay Time	$t_{d(on)}$	I_C = 80A, V_{CC} = 400V	-	45	-	ns
Rise Time	t_r	V_{GE} = 15V, R_G = 10Ω	-	29	-	
Turn - off Delay Time	$t_{d(off)}$	T_j = 25°C	-	201	-	
Fall Time	t_f	Inductive Load	-	34	-	
Turn - on Switching Loss	E_{on}	*E_{on} includes diode	-	2.65	-	mJ
Turn - off Switching Loss	E_{off}	reverse recovery	-	1.80	-	
Turn - on Delay Time	$t_{d(on)}$	I_C = 80A, V_{CC} = 400V	-	49	-	ns
Rise Time	t_r	V_{GE} = 15V, R_G = 10Ω	-	34	-	
Turn - off Delay Time	$t_{d(off)}$	T_j = 175°C	-	218	-	
Fall Time	t_f	Inductive Load	-	80	-	
Turn - on Switching Loss	E_{on}	*E_{on} includes diode	-	2.74	-	mJ
Turn - off Switching Loss	E_{off}	reverse recovery	-	2.31	-	
Reverse Bias Safe Operating Area	RBSOA	I_C = 320A, V_{CC} = 520V V_P = 650V, V_{GE} = 15V R_G = 100Ω, T_j = 175°C	FULL SQUARE			-
Short Circuit Withstand Time	t_{sc}	V_{CC} ≦ 360V V_{GE} = 15V T_j = 25°C	2	-	-	μs

●Electrical Characteristic Curves

Fig.1 Power Dissipation vs. Case Temperature

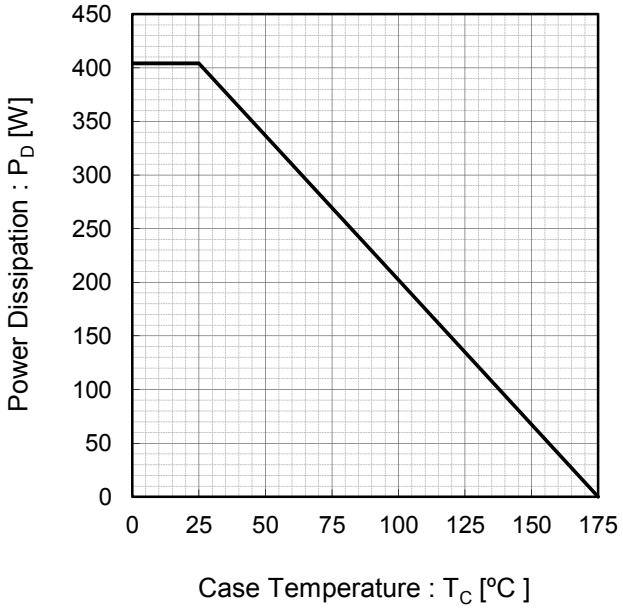


Fig.2 Collector Current vs. Case Temperature

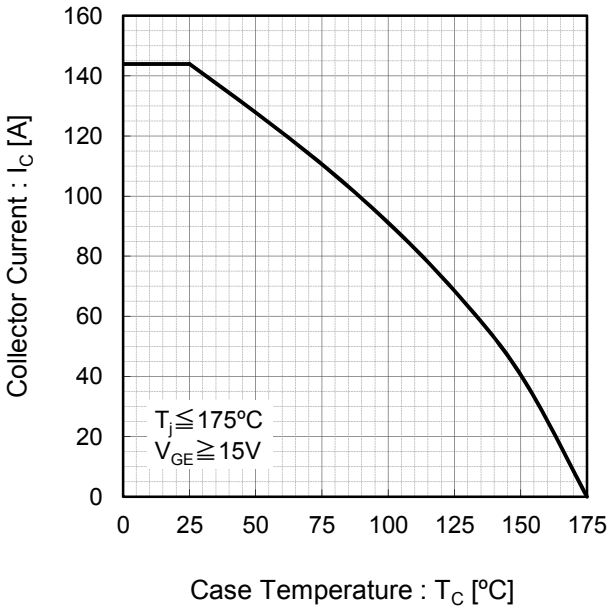


Fig.3 Forward Bias Safe Operating Area

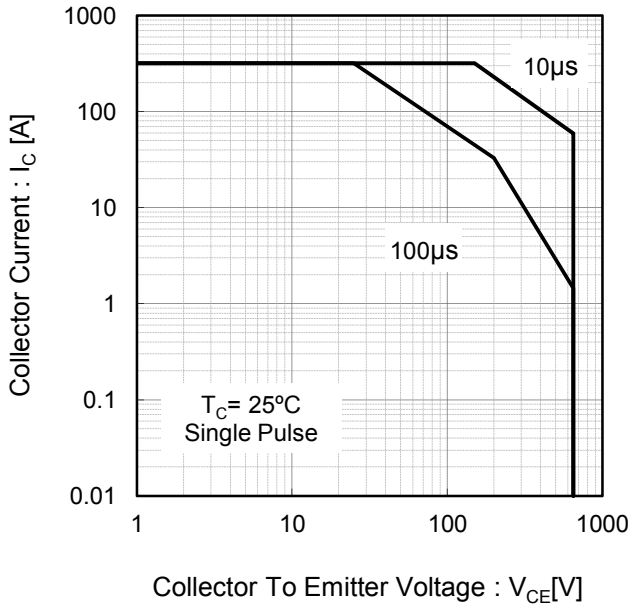
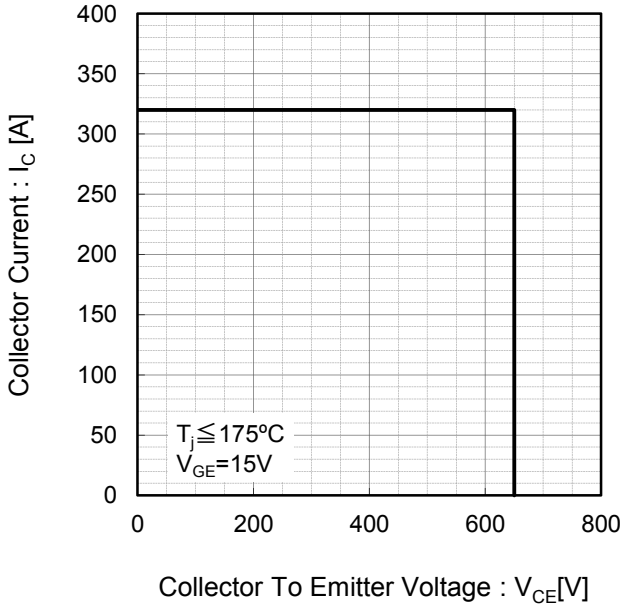


Fig.4 Reverse Bias Safe Operating Area



●Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

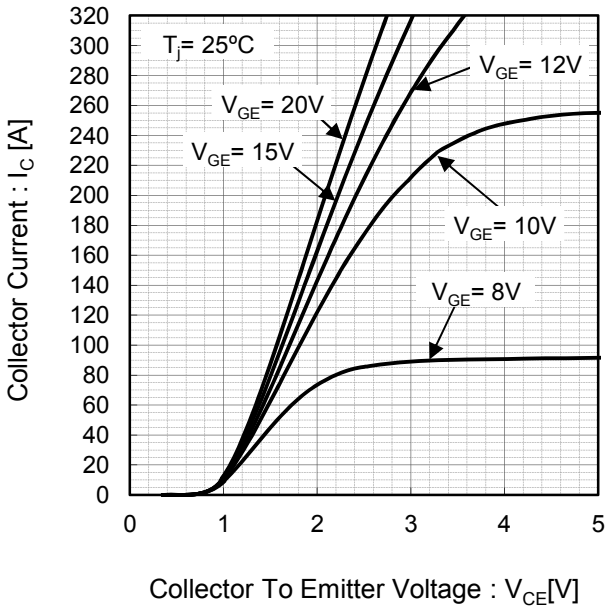


Fig.6 Typical Output Characteristics

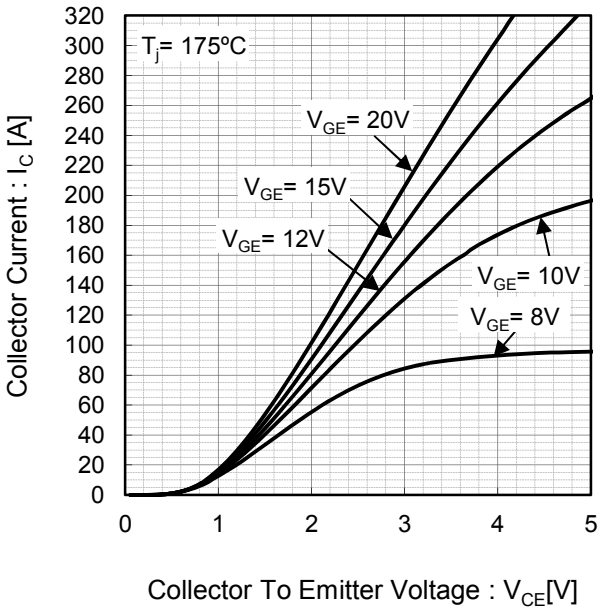


Fig.7 Typical Transfer Characteristics

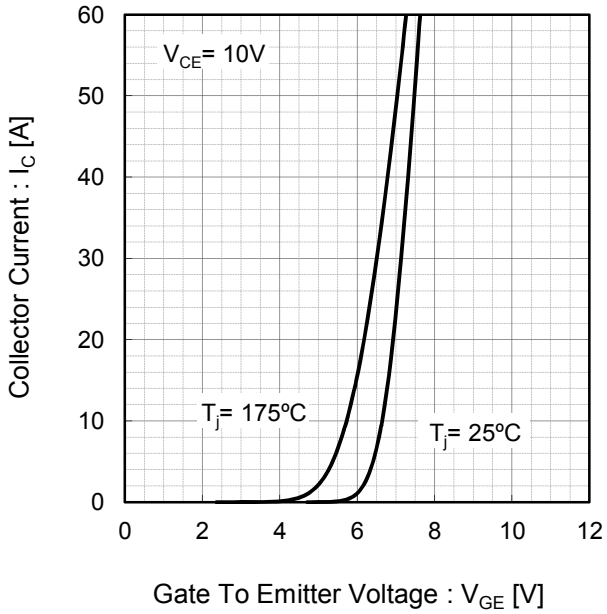
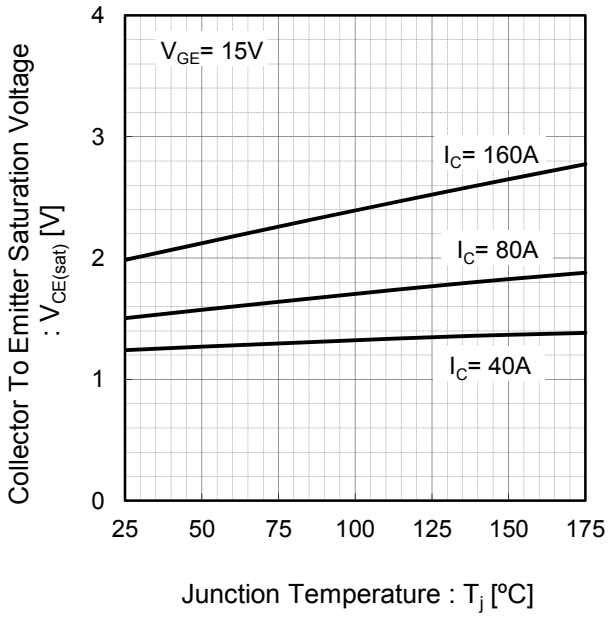


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



●Electrical Characteristic Curves

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

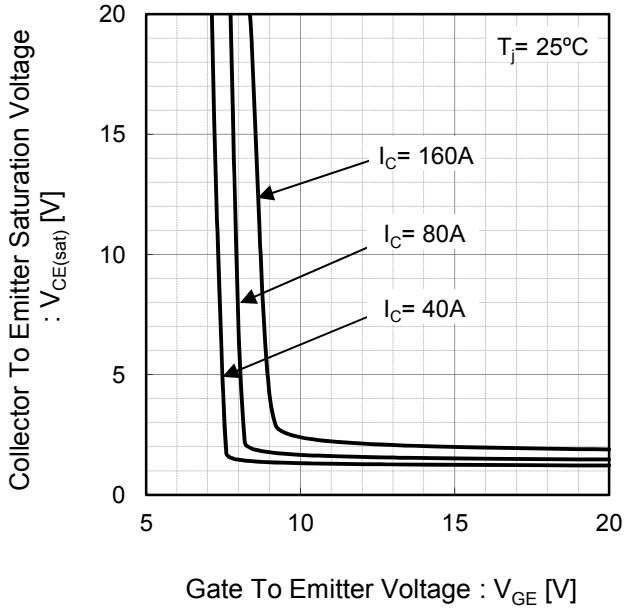


Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

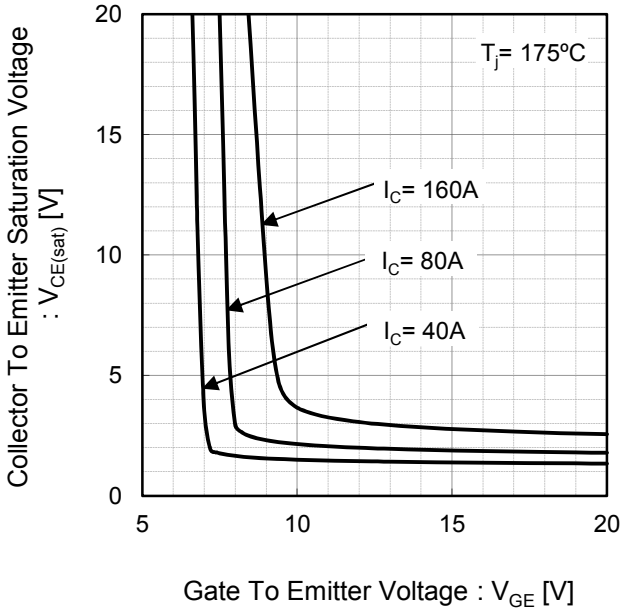


Fig.11 Typical Switching Time vs. Collector Current

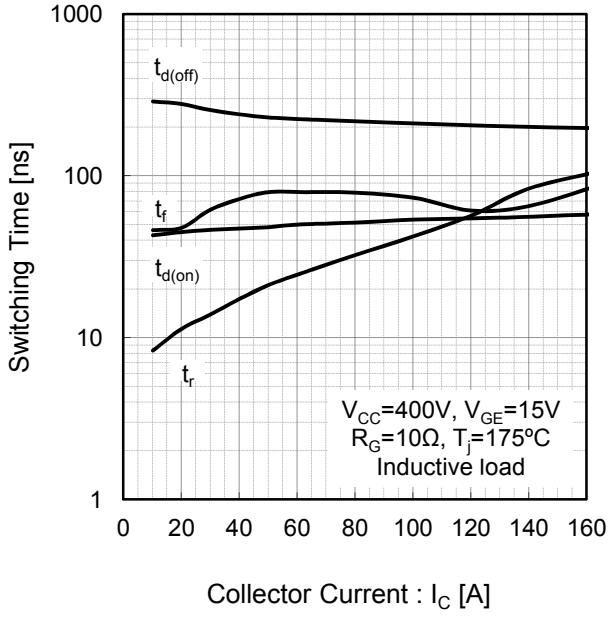
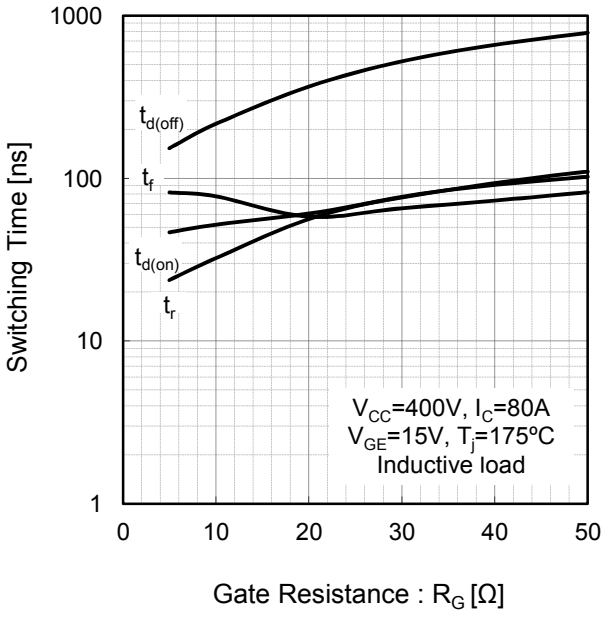


Fig.12 Typical Switching Time vs. Gate Resistance



●Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current

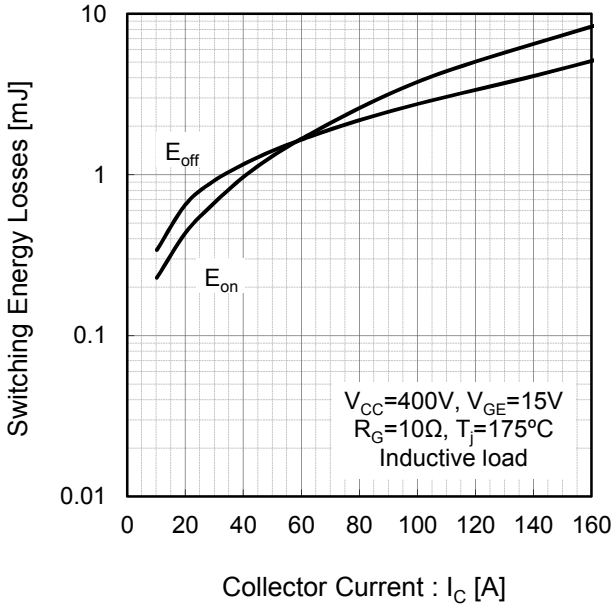


Fig.14 Typical Switching Energy Losses vs. Gate Resistance

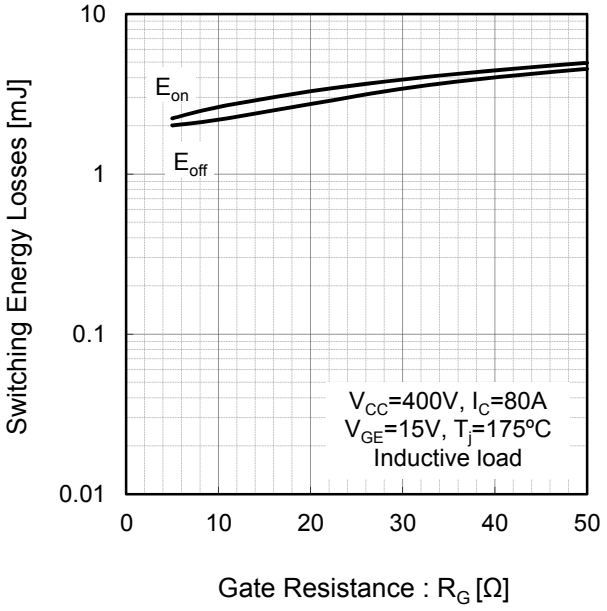


Fig.15 Typical Capacitance vs. Collector To Emitter Voltage

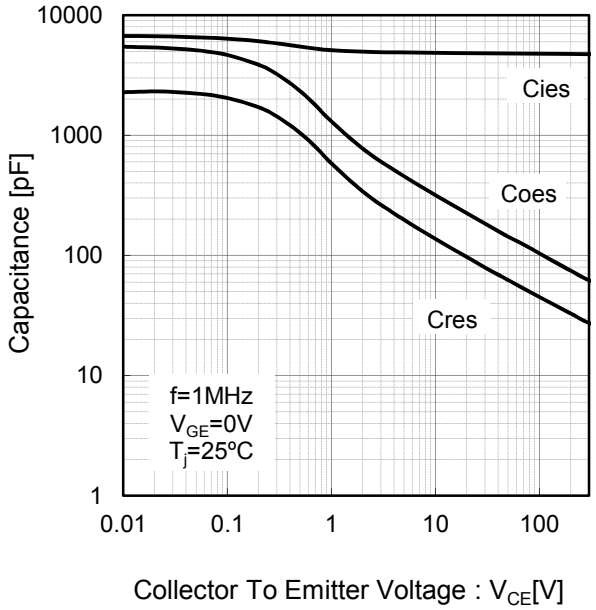
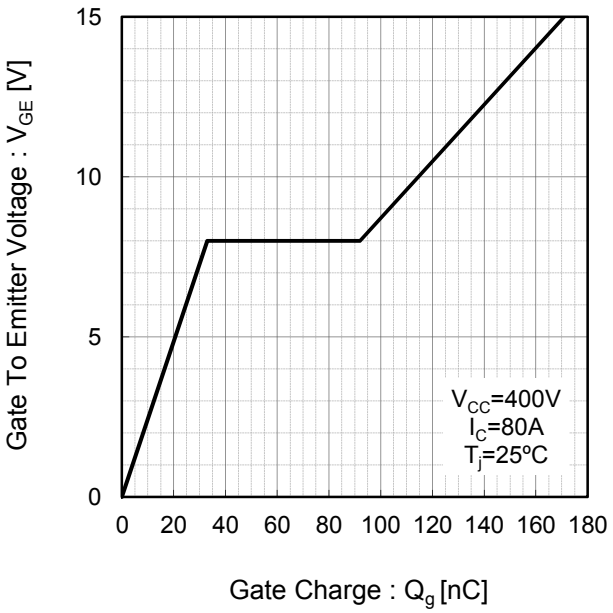
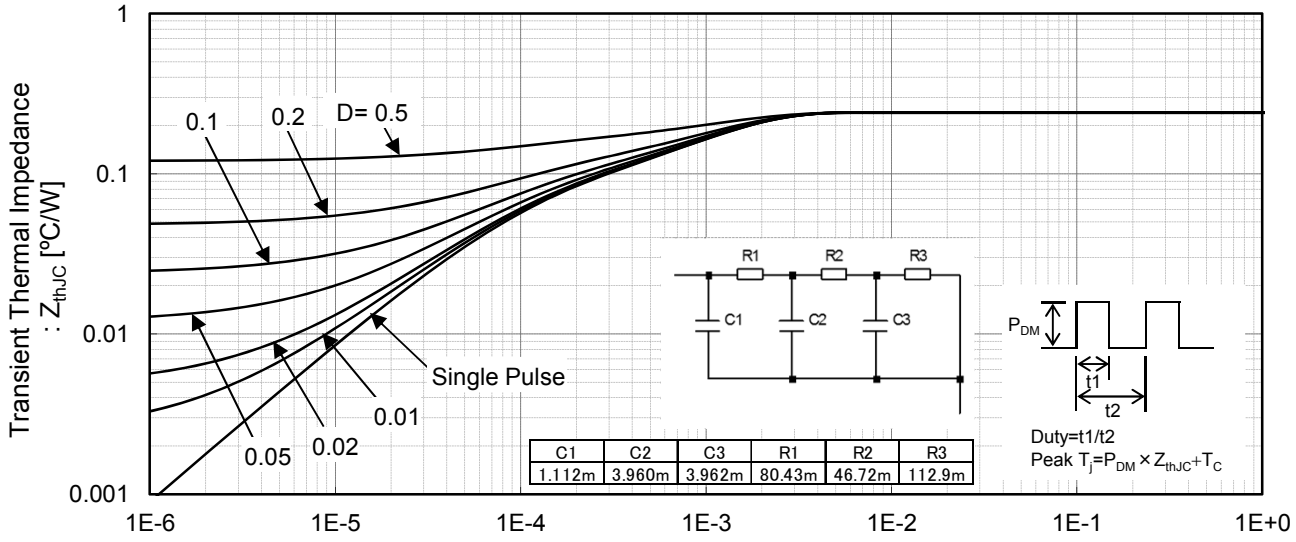


Fig.16 Typical Gate Charge



●Electrical Characteristic Curves

Fig.17 Typical IGBT Transient Thermal Impedance



C1	C2	C3	R1	R2	R3
1.112m	3.960m	3.962m	80.43m	46.72m	112.9m

Pulse Width : t1[s]

●Inductive Load Switching Circuit and Waveform

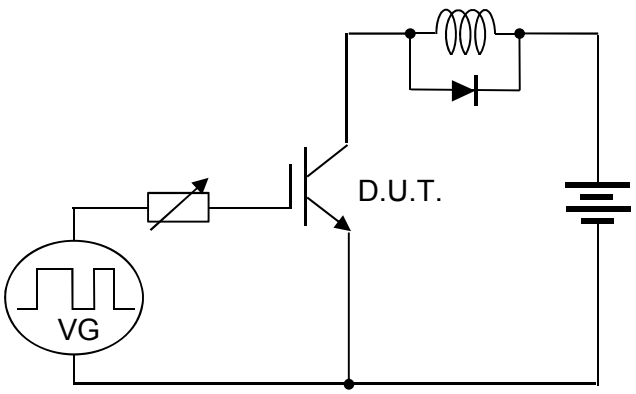


Fig.18 Inductive Load Circuit

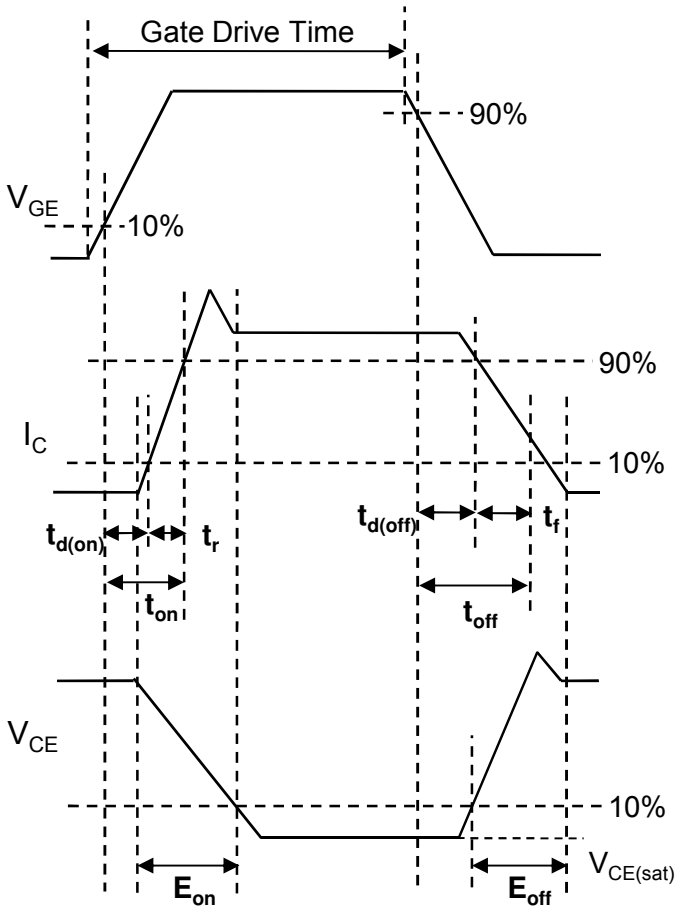


Fig.19 Inductive Load Waveform

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RGTVX6TS65 - Web Page

Part Number	RGTVX6TS65
Package	TO-247N
Unit Quantity	450
Minimum Package Quantity	30
Packing Type	Tube
Constitution Materials List	inquiry
RoHS	Yes